CERTIFICATE OF Applicant(s): Chan et al.	Docket No.			
		T	YO99842@IV	
Senal No.	Filing Date	Examiner	Group Art Unit	
10/051,562	January 18, 2002	Novacek, Christy L.	2822	
Invention: SELF-ALIGNED COUBLE-GATE MOSFET BY SELECTIVE EPITAXY AND SILICON WAFER				
BONDING TECHNIQUES RECEIVED				
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			APPIAI.	
I hereby certify that this		nendment Under 37 C.F.R. 1.11	₩ ₩ ₩ ₩ ₩ ₩	
(Identify type of correspondence)				
is being facsimile transmi	itted to the United States Patent	and Trademark Office (Fax.)	No. 703-872-9306)	
on February 3,	, 2004	•		
(Date)				
	Frederick W. Gibb, III			
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FICIAL

In re patent application of

Chan et al.

Serial No.: 10/051,562

Group Art Unit: 2822

Filed: January 18, 2002

Examiner: Novacek, Christy L.

For: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY AND

SILICON WAFER BONDING TECHNIQUES.

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action mailed November 4, 2003, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please amend the claims as follows.